	Typ	L #	Hit	S arch T xt	DB	Tim Stamp	C mm nts	Err r D finitl n	Err rs
7	BRS	L7	956	gallium adj nitrid	USPAT	2002/02/28 15:04			0
8	BRS	L8	78	gallium adj nitrogen	USPAT	2002/02/28 15:04			0
9	BRS	L9	3114	gan	USPAT	2002/02/28 15:04			0
10	BRS	L10	412	algan	USPAT	2002/02/28 15:04			0
11	BRS	L11	168	iii adj nitride	USPAT	2002/02/28 15:04			0
12	BRS	L12	102	iii adj v adj nitride	USPAT	2002/02/28 15:05			0
13	BRS	L13	467	(7 8 9 10 11 12).ti,ab.	USPAT	2002/02/28 15:05			0
14	BRS	L14	71	13 and dielectric	USPAT	2002/02/28 15:14			0
15	BRS	L15	10582	sio	USPAT	2002/02/28 15:15			0
16	BRS	L16	34291	sin	USPAT	2002/02/28 15:15			0
17	BRS	L17	6243	sion	USPAT	2002/02/28 15:15			0
18	BRS	L18	495	15 same 16	USPAT	2002/02/28 15:16			0
19	BRS	L19	2	18 and 372/46.ccls.	USPAT	2002/02/28 15:17			0
20	BRS	L20	419	h01s003/18 and gan	JPO	2002/02/28 15:17			0
21	BRS	L21	26	h01s003/18 and gan and	JPO	2002/02/28 15:23			0
22	BRS	L22	52	gan and sio	JPO	2002/02/28 15:23			0
23	BRS	L24	1	23 and sin	JPO	2002/02/28 15:24			0

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	Typ	L #	Hits	Search Text	DB	Tim Stamp	Comm nt	Error D finiti n	Err rs
24	BRS	L23	26	22 not 21	JPO	2002/02/28 15:28			0
25	BRS	L25	853	h01s003/18 and (nitride or nitrogen)	JPO	2002/02/28 15:29			0
26	BRS	L26	147	h01s003/18 and (nitride or nitrogen) and (sio or tio or insulat$ or dielectric)	JPO	2002/02/28 15:30			0
27	BRS	L27	28	h01s003/18 and (gan or algan or ingaasn or gaasn or bn)	JPO	2002/02/28 15:32			0
28	BRS	L29	823	sio with sin	JPO	2002/02/28 15:34			0
29	BRS	L30	336	29 and ((semiconducto r or diode$1) near2 (laser$ or device$))	JPO	2002/02/28 15:34			0
30	BRS	L31	1	sio with sin with grad$	JPO	2002/02/28 15:34			0
31	BRS	L32	11057	oxide with nitride	JPO	2002/02/28 15:34			0
32	BRS	L33	42	32 and (h01s003/18 or h01s005/00)	JPO	2002/02/28 15:40			0
33	BRS	L34	0	oxynitride and gan	JPO	2002/02/28 15:40			0
34	BRS	L35	0	oxynitride and algan	JPO	2002/02/28 15:40			0

	Typ	L #	Hits	S arch T xt	DBs	Tim Stamp	C mm nts	Error D finiti n	Errors
35	BRS	L36	4	xynitrid and algan	USPAT	2002/02/28 15:41			0
36	BRS	L37	8	oxynitride and 372/46$.ccls.	USPAT	2002/02/28 15:46			0
37	BRS	L38	153	372/46,45.ccls. and gan	USPAT	2002/02/28 15:46			0
38	BRS	L39	331928	LD or LED or VCSEL or VCSELS or diode or diodes or RCLED or RCLEDs or RCPD or RCPDs or LDs or LEDs	USPAT	2002/02/28 16:07			0
39	BRS	L40	19092	gan or aln or inn or bn or tln	USPAT	2002/02/28 16:07			0
40	BRS	L41	3908	39 and 40	USPAT	2002/02/28 16:08			0
41	BRS	L42	2154	41 and (oxynitride or oxide or nitride)	USPAT	2002/02/28 16:08			0
42	BRS	L43	57	41 and (oxynitride and oxide and nitride)	USPAT	2002/02/28 16:40			0
43	BRS	L44	8	372/46.ccls. and oxynitride	USPAT	2002/02/28 16:40			0
44	BRS	L45	0	44 and gan	USPAT	2002/02/28 16:40			0
45	BRS	L46	50	oxynitride and gan	USPAT	2002/02/28 16:45			0
46	BRS	L47	9	sion and 372/46. cls.	USPAT	2002/02/28 16:45			0

	Typ	L #	Hits	S arch T xt	DB	Tim Stamp	C mm nts	Err r D finiti n	Err rs
47	BRS	L48	0	si n and 372/46.ccls. and nitride	USPAT	2002/02/28 16:45			0
48	BRS	L49	0	sion and 372/46.ccls. and gan	USPAT	2002/02/28 16:45			0